N-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	100V
● I_D	149A
● $R_{DS(ON)}$(at V_{GS}=10V)	4.6mΩ

● 100% EAS Tested

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units

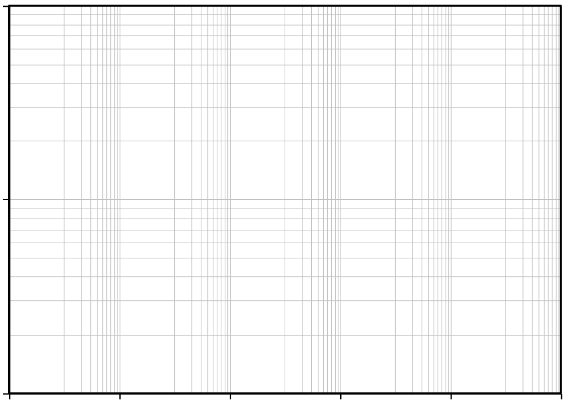


Figure 13. Maximum Transient Thermal Impedance

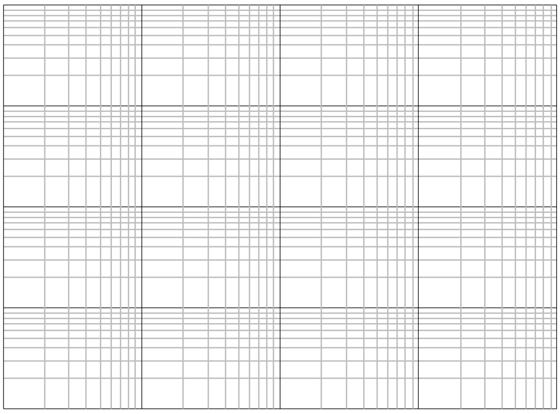
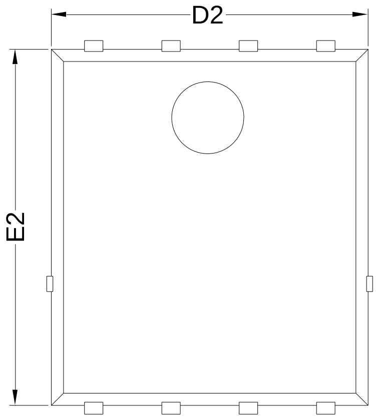
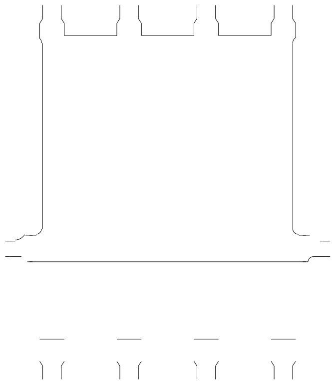


Figure 14. Safe Operation Area

■ PDFN5060-8L-B-1.1MM Package information



Top View



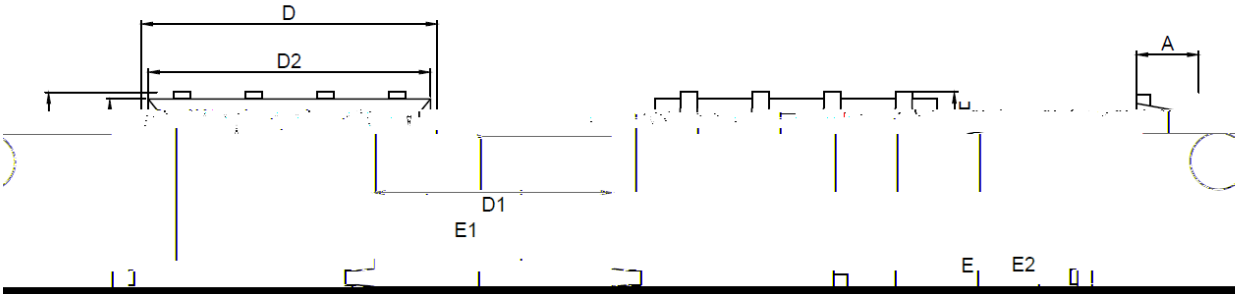
Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

■ PDFN5060-8L-H-1.1MM Package information



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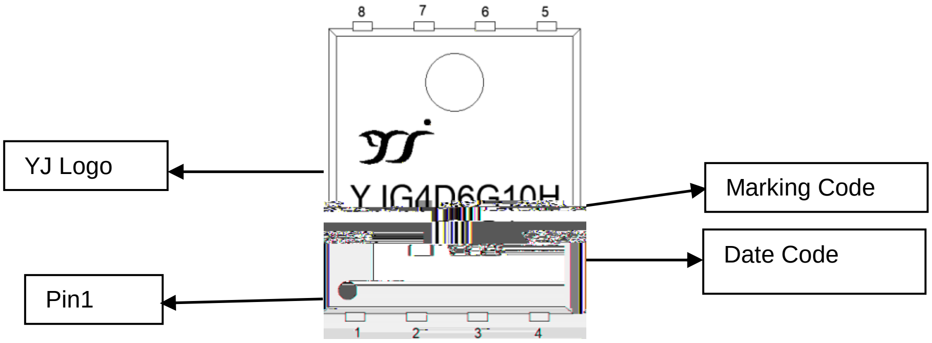
■ Marking Information



Note
1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJG4D6G10H is Marking Code, YYWW is date code, “YY” is year, “WW” is week
4. Body color: Black

Disclaimer